



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Ι _D T _A = +25°C
300V	4Ω @ V _{GS} = 10V	0.25A
3007	4Ω @ V _{GS} = 4.5V	0.25A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Description and Applications

- DC-DC Converters
- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc



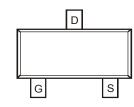
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

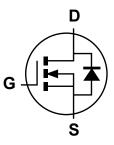
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 (3)
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Top View



Top View Pin Configuration



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN30H4D0L-7	SOT23	3,000/Tape & Reel
DMN30H4D0L-13	SOT23	10,000/Tape & Reel

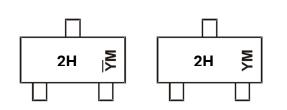
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2H = Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Notes:

Year	201	3	2014		2015	20	16	2017		2018	2	2019
Code	A		В		С	[)	E		F		G
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	V		
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	T _A = +25°C T _A = +70°C	ID	0.25 0.20	А
Pulsed Drain Current (10µs pulse, duty cycle ≦1%)	I _{DM}	2	А	
Maximum Body Diode Continuous Current (Note 6)	Is	0.8	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Power Dissipation	(Note 5)	D	0.31	W	
	(Note 6)	PD	0.47		
Thermal Decistance Junction to Ambient	(Note 5)		377		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ extsf{ heta}JA}$	255	°C/W	
Thermal Resistance, Junction to Case	$R_{ ext{ heta}JC}$	81			
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to 150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	300	_		V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	V _{DS} = 240V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	1	_	3	V	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	
		_	2.1	4		V _{GS} = 10V, I _D = 0.3A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2.1	4	Ω	V _{GS} = 4.5V, I _D = 0.2A	
		_	3.8	6		V _{GS} = 2.7V, I _D = 0.1A	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 0.3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	187.3				
Output Capacitance	C _{oss}	_	11.7		pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	8.7				
Total Gate Charge	Qg	_	7.6	_			
Gate-Source Charge	Q _{gs}	_	0.5	_	nC	V _{DS} = 192V, V _{GS} = 10V, I _D = 0.5A	
Gate-Drain Charge	Q _{gd}	_	3.3	_		ID - 0.5A	
Turn-On Delay Time	t _{D(on)}	_	4.9				
Turn-On Rise Time	tr	_	4.7		nS	V _{DS} = 60V, R _L =200Ω	
Turn-Off Delay Time	t _{D(off)}	_	25.8		115	V_{GS} = 10V, R_G = 25 Ω	
Turn-Off Fall Time	tf		17.5				

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout

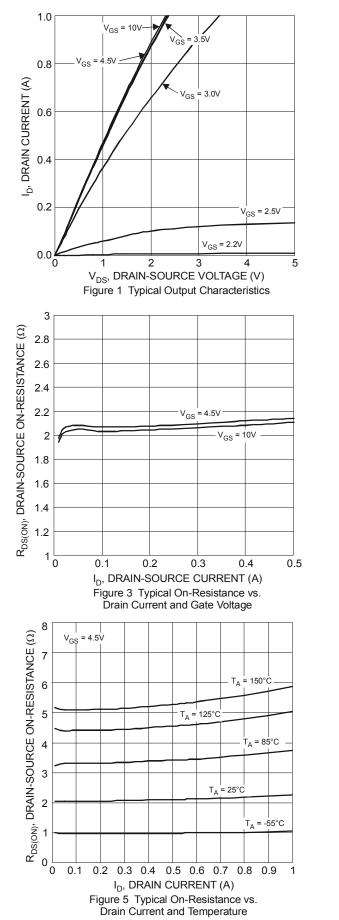
7 .Short duration pulse test used to minimize self-heating effect.

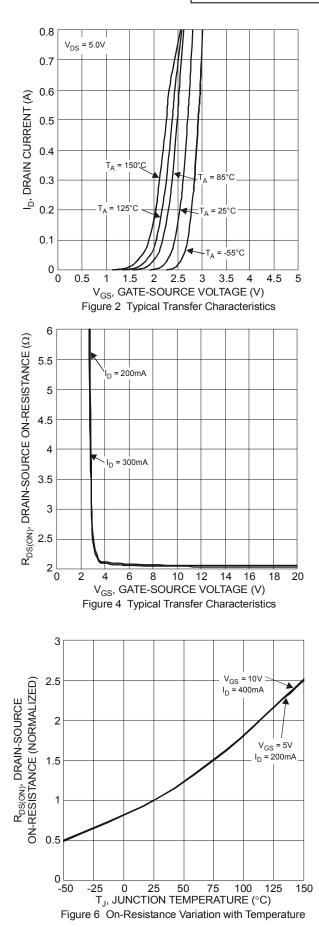
8. Guaranteed by design. Not subject to production testing.

Notes:



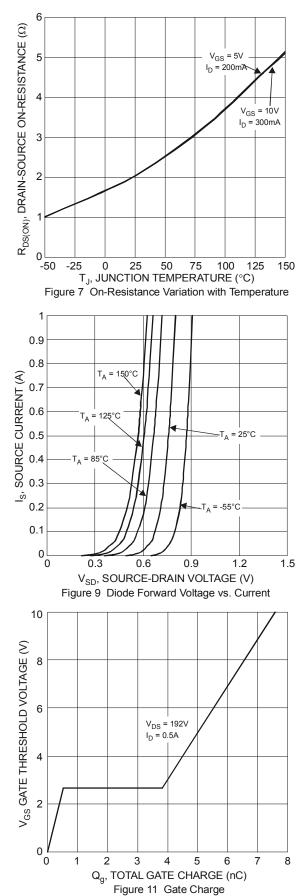


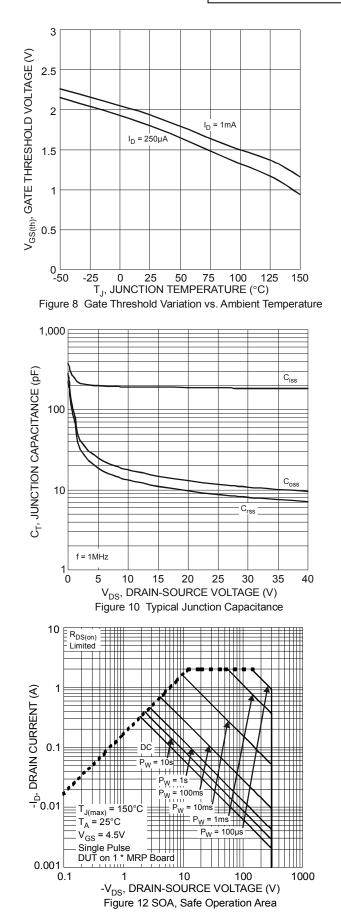




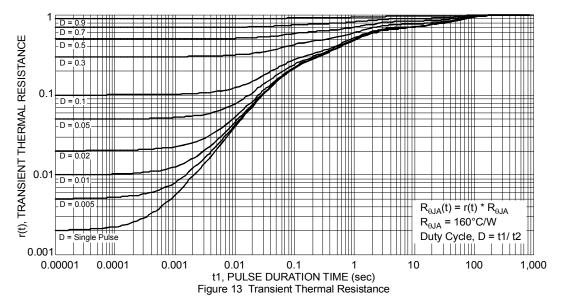






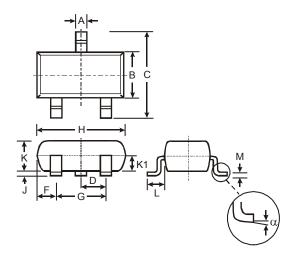






Package Outline Dimensions

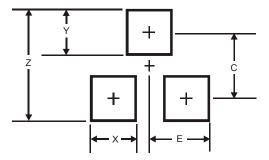
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
в	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
н	2.80	3.00	2.90				
ر	0.013	0.10	0.05				
κ	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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